Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	335755	semiconductor and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:15
L2	132506	1 and gate and source and drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:16
L3	85430	2 and channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:17
L4	46311	3 and (gate adj electrode)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:18
L5	14188	4 and surround$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:19
L6	3694	5 and perpendicular	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:22
L7	3439	6 and side	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:25
L8	3343	7 and surface	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:26

L9	2619	8 and plurality	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:26
L10	2547	9 and insulat$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:29
L11	2360	10 and (top or upper)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/26 16:29